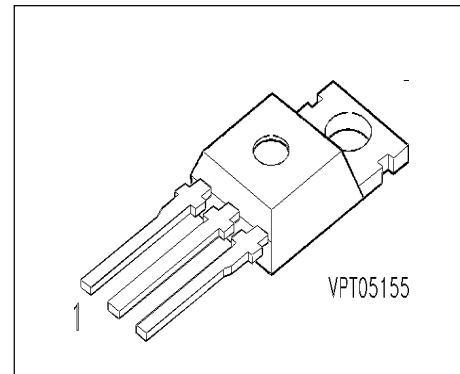


SIPMOS[®] Power Transistor

- N channel
- Enhancement mode
- Avalanche-rated
- Logic Level

BUZ 72AL



Pin 1	Pin 2	Pin 3
G	D	S

Type	V _{DS}	I _D	R _{DS(on)}	Package	Ordering Code
BUZ 72 AL	100 V	9 A	0.25 Ω	TO-220 AB	C67078-S1327-A3

Maximum Ratings

Parameter	Symbol	Values	Unit
Continuous drain current <i>T_C</i> = 25 °C	I _D	9	A
Pulsed drain current <i>T_C</i> = 25 °C	I _{Dpuls}	36	
Avalanche current, limited by <i>T_{jmax}</i>	I _{AR}	10	
Avalanche energy, periodic limited by <i>T_{jmax}</i>	E _{AR}	7.9	mJ
Avalanche energy, single pulse I _D = 10 A, V _{DD} = 25 V, R _{GS} = 25 Ω L = 885 μH, <i>T_j</i> = 25 °C	E _{AS}	59	
Gate source voltage	V _{GS}	± 20	V
ESD-Sensitivity HBM as per MIL-STD 883		Class 1	
Power dissipation <i>T_C</i> = 25 °C	P _{tot}	40	W
Operating temperature	<i>T_j</i>	-55 ... + 150	°C
Storage temperature	<i>T_{stg}</i>	-55 ... + 150	
Thermal resistance, chip case	R _{thJC}	≤ 3.1	K/W
Thermal resistance, chip to ambient	R _{thJA}	75	
DIN humidity category, DIN 40 040		E	
IEC climatic category, DIN IEC 68-1		55 / 150 / 56	

Electrical Characteristics, at $T_j = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Static Characteristics					
Drain- source breakdown voltage $V_{GS} = 0\text{ V}, I_D = 0.25\text{ mA}, T_j = 25^\circ\text{C}$	$V_{(BR)DSS}$	100	-	-	V
Gate threshold voltage $V_{GS}=V_{DS}, I_D = 1\text{ mA}$	$V_{GS(th)}$	1.2	1.6	2	
Zero gate voltage drain current $V_{DS} = 100\text{ V}, V_{GS} = 0\text{ V}, T_j = 25^\circ\text{C}$ $V_{DS} = 100\text{ V}, V_{GS} = 0\text{ V}, T_j = 125^\circ\text{C}$	I_{DSS}	-	0.1 10	1 100	μA
Gate-source leakage current $V_{GS} = 20\text{ V}, V_{DS} = 0\text{ V}$	I_{GSS}	-	10	100	nA
Drain-Source on-resistance $V_{GS} = 5\text{ V}, I_D = 5\text{ A}$	$R_{DS(on)}$	-	0.15	0.25	Ω

Electrical Characteristics, at $T_j = 25^\circ\text{C}$, unless otherwise specified

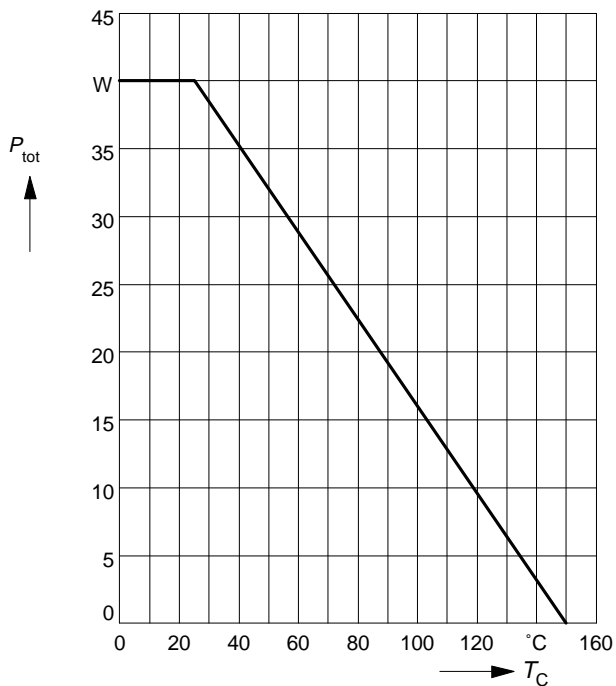
Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Dynamic Characteristics					
Transconductance $V_{DS} \geq 2 * I_D * R_{DS(on)max}, I_D = 5 \text{ A}$	g_{fs}	5	7.5	-	S
Input capacitance $V_{GS} = 0 \text{ V}, V_{DS} = 25 \text{ V}, f = 1 \text{ MHz}$	C_{iss}	-	680	900	pF
Output capacitance $V_{GS} = 0 \text{ V}, V_{DS} = 25 \text{ V}, f = 1 \text{ MHz}$	C_{oss}	-	180	250	
Reverse transfer capacitance $V_{GS} = 0 \text{ V}, V_{DS} = 25 \text{ V}, f = 1 \text{ MHz}$	C_{rss}	-	90	150	
Turn-on delay time $V_{DD} = 30 \text{ V}, V_{GS} = 5 \text{ V}, I_D = 3 \text{ A}$ $R_{GS} = 50 \Omega$	$t_{d(on)}$	-	20	30	ns
Rise time $V_{DD} = 30 \text{ V}, V_{GS} = 5 \text{ V}, I_D = 3 \text{ A}$ $R_{GS} = 50 \Omega$	t_r	-	85	130	
Turn-off delay time $V_{DD} = 30 \text{ V}, V_{GS} = 5 \text{ V}, I_D = 3 \text{ A}$ $R_{GS} = 50 \Omega$	$t_{d(off)}$	-	100	130	
Fall time $V_{DD} = 30 \text{ V}, V_{GS} = 5 \text{ V}, I_D = 3 \text{ A}$ $R_{GS} = 50 \Omega$	t_f	-	55	70	

Electrical Characteristics, at $T_j = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Reverse Diode					
Inverse diode continuous forward current $T_C = 25^\circ\text{C}$	I_S	-	-	9	A
Inverse diode direct current,pulsed $T_C = 25^\circ\text{C}$	I_{SM}	-	-	36	
Inverse diode forward voltage $V_{GS} = 0\text{ V}, I_F = 20\text{ A}$	V_{SD}	-	1.2	1.5	V
Reverse recovery time $V_R = 30\text{ V}, I_F = I_S, di_F/dt = 100\text{ A}/\mu\text{s}$	t_{rr}	-	180	-	ns
Reverse recovery charge $V_R = 30\text{ V}, I_F = I_S, di_F/dt = 100\text{ A}/\mu\text{s}$	Q_{rr}	-	460	-	nC

Power dissipation

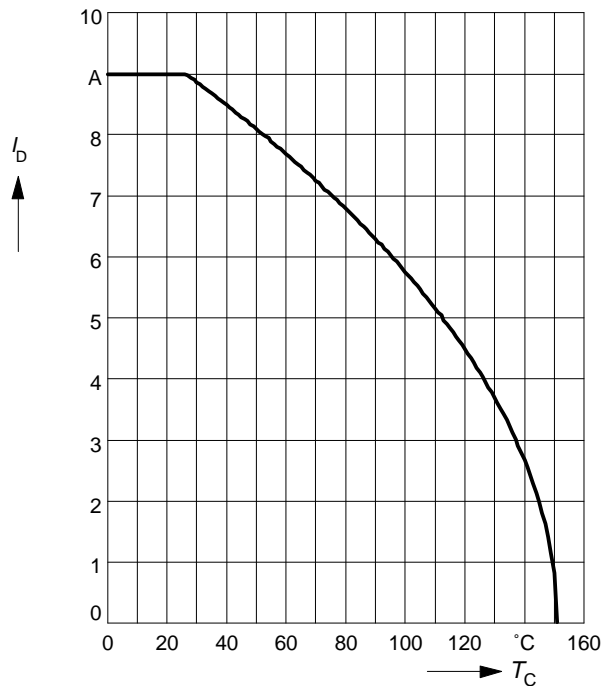
$P_{tot} = f(T_C)$



Drain current

$I_D = f(T_C)$

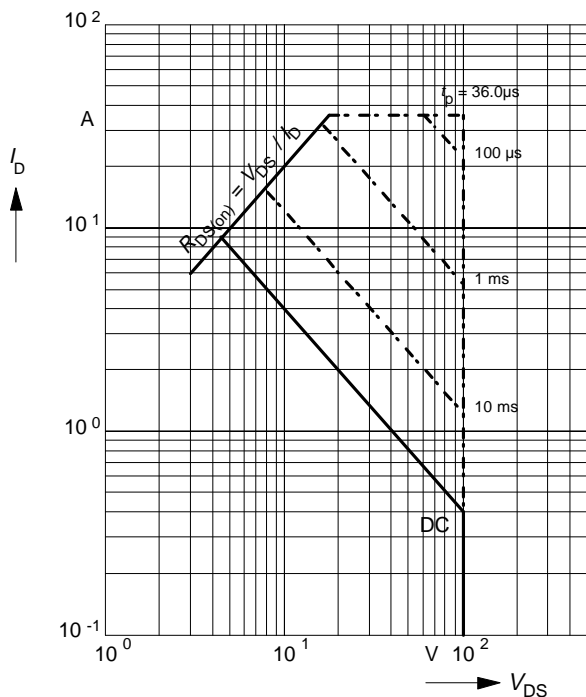
parameter: $V_{GS} \geq 5 \text{ V}$



Safe operating area

$I_D = f(V_{DS})$

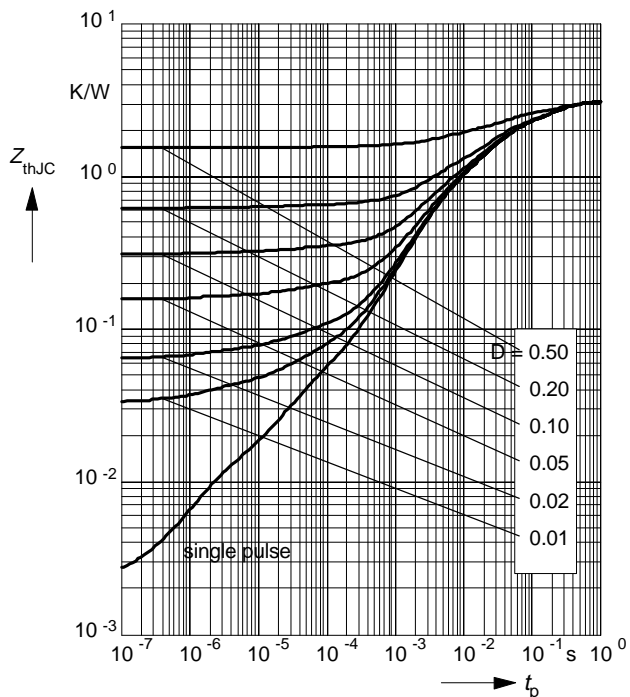
parameter: $D = 0.01, T_C = 25^\circ\text{C}$



Transient thermal impedance

$Z_{thJC} = f(t_p)$

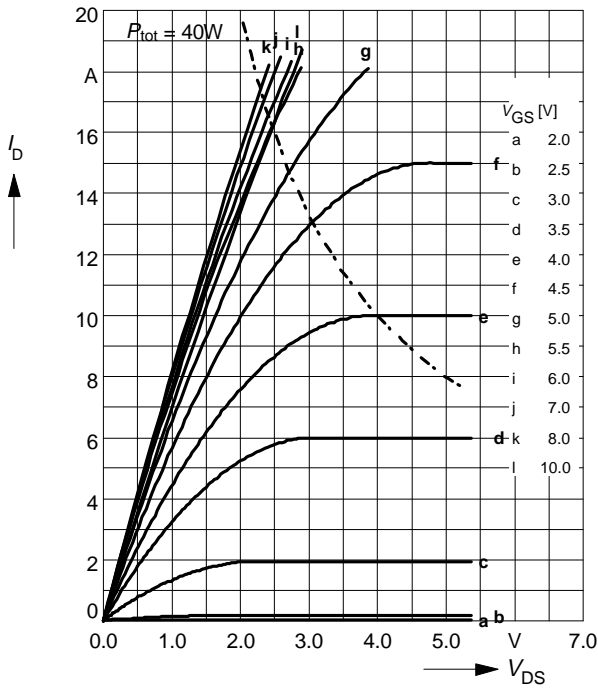
parameter: $D = t_p / T$



Typ. output characteristics

$I_D = f(V_{DS})$

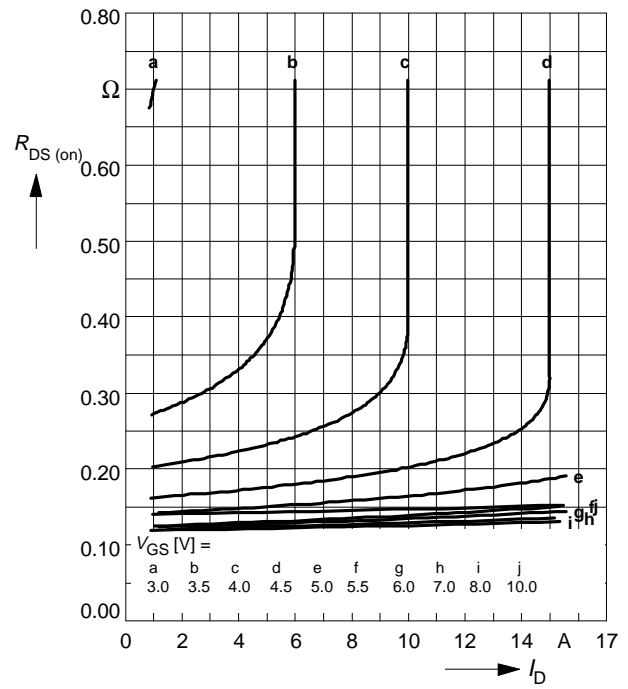
parameter: $t_p = 80 \mu s$



Typ. drain-source on-resistance

$R_{DS(on)} = f(I_D)$

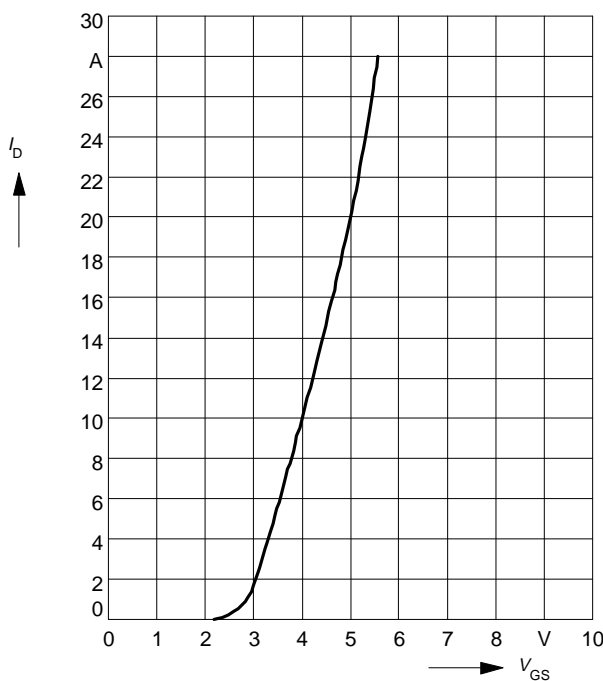
parameter: V_{GS}



Typ. transfer characteristics $I_D = f(V_{GS})$

parameter: $t_p = 80 \mu s$

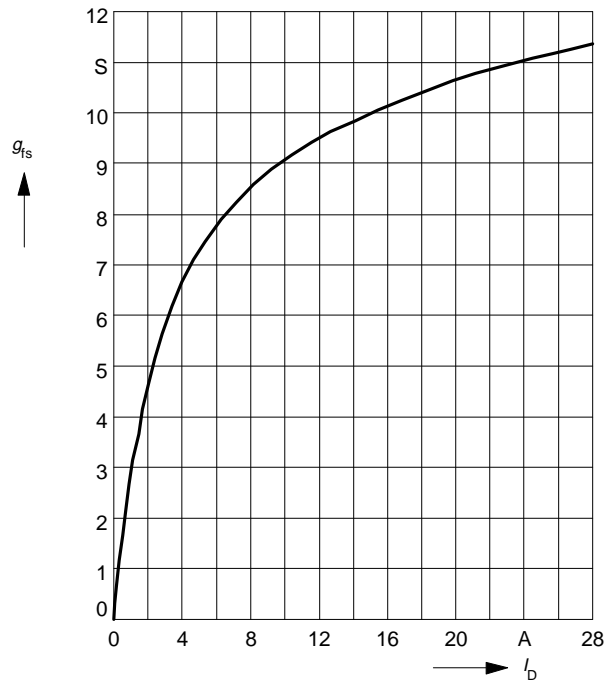
$V_{DS} \geq 2 \times I_D \times R_{DS(on)max}$



Typ. forward transconductance $g_{fs} = f(I_D)$

parameter: $t_p = 80 \mu s$,

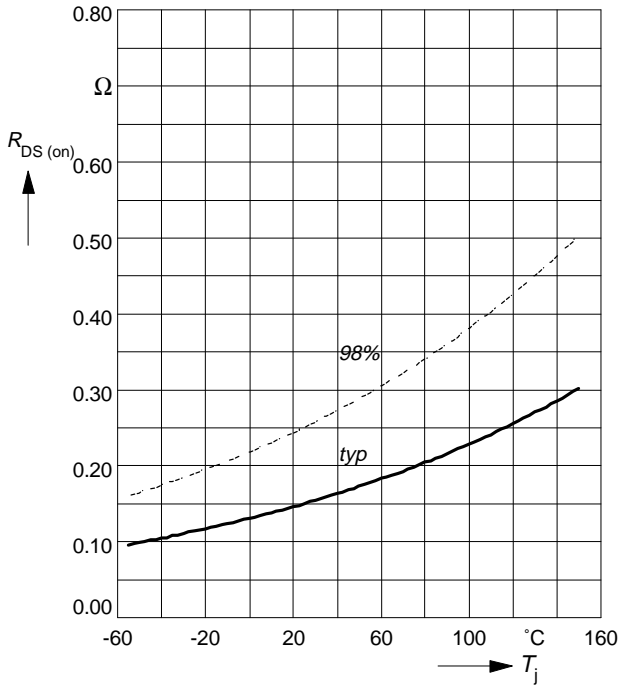
$V_{DS} \geq 2 \times I_D \times R_{DS(on)max}$



Drain-source on-resistance

$R_{DS(on)} = f(T_j)$

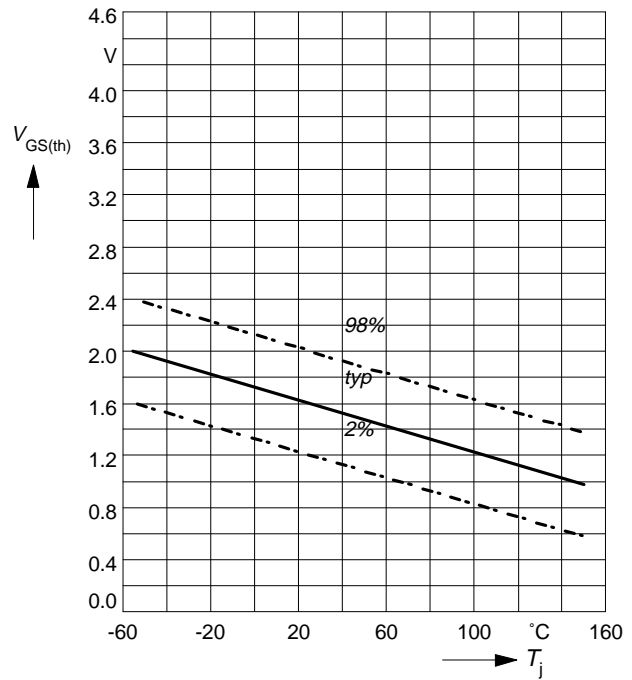
parameter: $I_D = 5\text{ A}$, $V_{GS} = 5\text{ V}$



Gate threshold voltage

$V_{GS(th)} = f(T_j)$

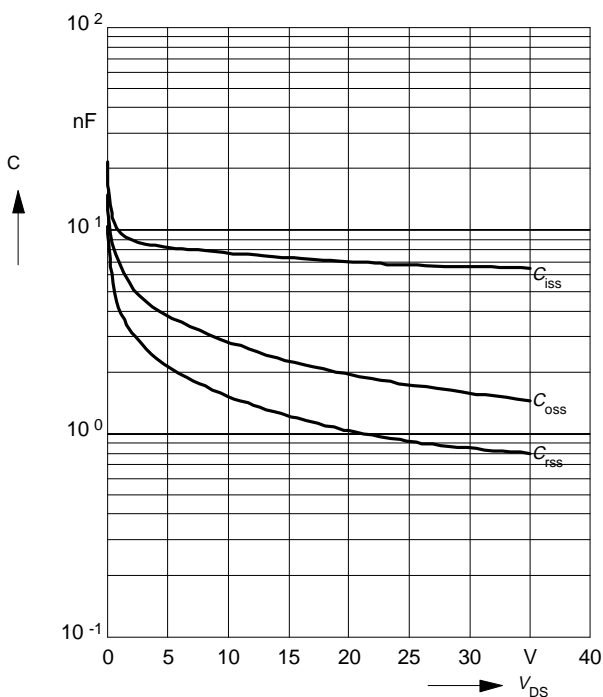
parameter: $V_{GS} = V_{DS}$, $I_D = 1\text{ mA}$



Typ. capacitances

$C = f(V_{DS})$

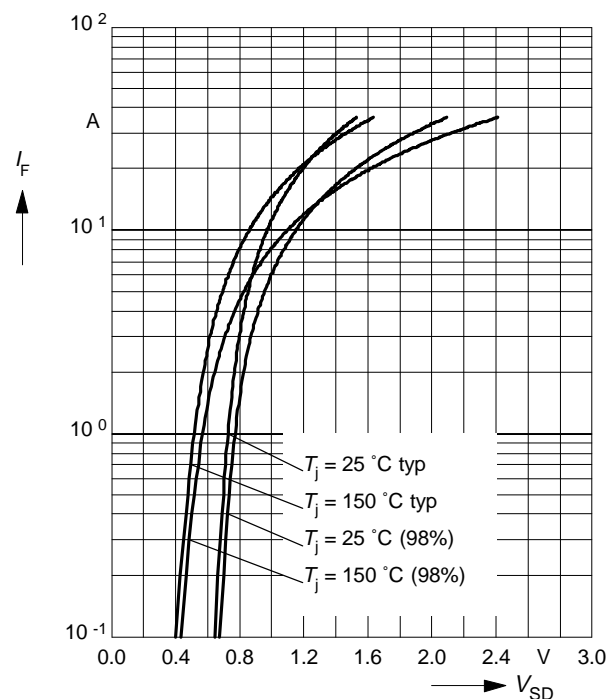
parameter: $V_{GS} = 0\text{ V}$, $f = 1\text{ MHz}$



Forward characteristics of reverse diode

$I_F = f(V_{SD})$

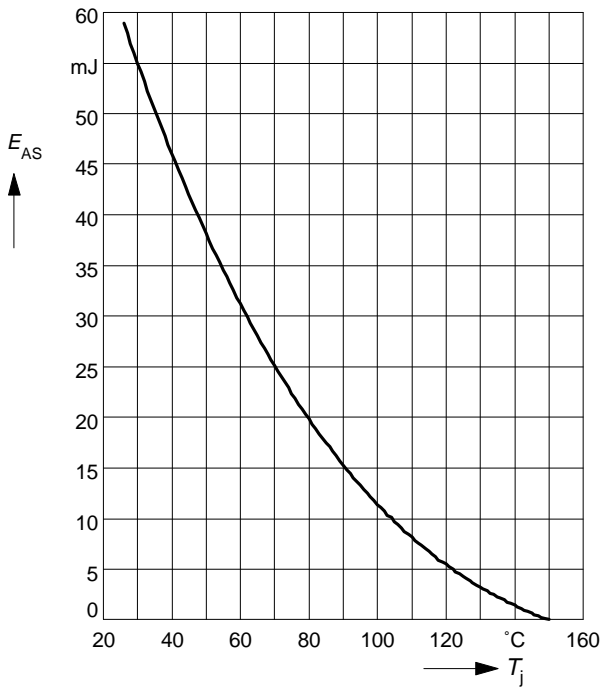
parameter: $T_j, t_p = 80\text{ }\mu\text{s}$



Avalanche energy $E_{AS} = f(T_j)$

parameter: $I_D = 10\text{ A}$, $V_{DD} = 25\text{ V}$

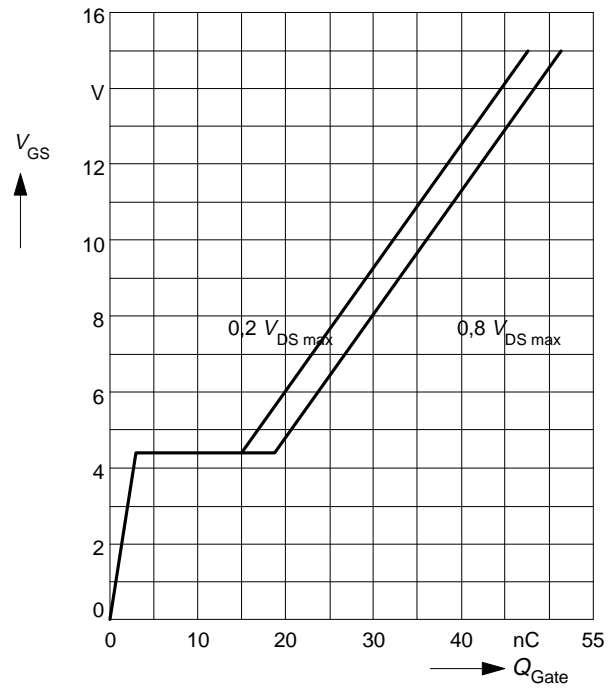
$R_{GS} = 25\ \Omega$, $L = 885\ \mu\text{H}$



Typ. gate charge

$V_{GS} = f(Q_{Gate})$

parameter: $I_{D\text{ puls}} = 15\text{ A}$



Drain-source breakdown voltage

$V_{(BR)DSS} = f(T_j)$

